

Eun Kyu Kim

List of Publications by Year in descending order

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times ranked

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#	ARTICLE	IF	CITATIONS
1	Effect of oxygen on defect states of Al _{0.4} Ga _{0.6} N layers grown by hydride vapor phase epitaxy. Journal of Materials Research and Technology, 2022, 17, 1485-1490.	2.6	2
2	Structural Analysis of InAs _{1-x} Sb _x Epilayer Considering Occurrence of Crystallographic Tilt Exploiting High-Resolution X-Ray Diffraction. Electronic Materials Letters, 2022, 18, 205-214.	1.0	0
3	High-performance MoS ₂ /p+-Si heterojunction field-effect transistors by interface modulation. Nano Research, 2022, 15, 6500-6506.	5.8	7
4	Electronic transport mechanism and defect states for p-InP/i-InGaAs/n-InP photodiodes. Journal of Materials Research and Technology, 2022, 19, 2742-2749.	2.6	3
5	Defect suppression and photoresponsivity enhancement in methylammonium lead halide perovskites by CdSe/ZnS quantum dots. Journal of Colloid and Interface Science, 2021, 590, 19-27.	5.0	11
6	Structural characteristics and defect states of intrinsic GaN epi-layers in a high power device structure. Journal of the Korean Physical Society, 2021, 79, 57-63.	0.3	2
7	Optimization of optoelectrical properties during synthesizing methylammonium lead iodide perovskites via a two-step dry process. Journal of Materials Research and Technology, 2021, 14, 1-9.	2.6	4
8	Post-annealing effects on Si-doped Ga ₂ O ₃ photodetectors grown by pulsed laser deposition. Journal of Alloys and Compounds, 2021, 877, 160291.	2.8	36
9	Performance Enhancement of a ZnO-based UV Photodetector Using Patterned Ag Nanoparticles. Journal of the Korean Physical Society, 2020, 77, 234-239.	0.3	1
10	Polarization-Sensitive and Wide Incidence Angle-Insensitive Fabry-Pérot Optical Cavity Bounded by Two Metal Grating Layers. Sensors, 2020, 20, 5382.	2.1	2
11	Plasmonic-Layered InAs/InGaAs Quantum-Dots-in-a-Well Pixel Detector for Spectral-Shaping and Photocurrent Enhancement. Nanomaterials, 2020, 10, 1827.	1.9	3
12	Photoelectric Characteristics of a Large-Area n-MoS ₂ /p-Si Heterojunction Structure Formed through Sulfurization Process. Sensors, 2020, 20, 7340.	2.1	7
13	Influence of titanium adhesion layer on performance of ¹² C-Ga ₂ O ₃ solar-blind photodetector. Materials Chemistry and Physics, 2020, 252, 123248.	2.0	3
14	Analysis of ZnS and MgF ₂ layered nanostructures grown by glancing angle deposition for optical design. Nanotechnology, 2020, 31, 245301.	1.3	1
15	The enhancement mechanism of photo-response depending on oxygen pressure for Ga ₂ O ₃ photo detectors. Nanotechnology, 2020, 31, 245201.	1.3	15
16	Current Transport Mechanism in Palladium Schottky Contact on Si-Based Freestanding GaN. Nanomaterials, 2020, 10, 297.	1.9	13
17	Long-Term Chemical Aging of Hybrid Halide Perovskites. Nano Letters, 2019, 19, 5604-5611.	4.5	13
18	The effect of oxygen partial pressure on band gap modulation of Ga ₂ O ₃ grown by pulsed laser deposition. Journal of Alloys and Compounds, 2019, 806, 874-880.	2.8	40

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19	Defect states of organic lead halide single crystals grown by inverse-temperature crystallization. Applied Physics Letters, 2019, 115, .	1.5	9
20	Characteristics of p-Type Conduction in P-Doped MoS ₂ by Phosphorous Pentoxide during Chemical Vapor Deposition. Nanomaterials, 2019, 9, 1278.	1.9	24
21	Antireflection Coatings with Graded Refractive Index of Indium Tin Oxide for Si-based Solar Cells. Journal of the Korean Physical Society, 2019, 74, 127-131.	0.3	9
22	First observation of electronic trap levels in freestanding GaN crystals extracted from Si substrates by hydride vapour phase epitaxy. Scientific Reports, 2019, 9, 7128.	1.6	5
23	Performance of thyristor memory device formed by a wet etching process. Nanotechnology, 2019, 30, 035205.	1.3	1
24	Hole Conduction of Tungsten Diselenide Crystalline Transistors by Niobium Dopant. Advanced Electronic Materials, 2019, 5, 1800695.	2.6	7
25	Formation of transition metal dichalcogenides thin films with liquid phase exfoliation technique and photovoltaic applications. Solar Energy Materials and Solar Cells, 2018, 184, 9-14.	3.0	16
26	High performance intermediate-band solar cells based on ZnTe:Cr with ZnO:Al electron transport layer. Solar Energy, 2018, 164, 262-266.	2.9	10
27	Recent Advances in Synthesis and Assembly of van der Waals Materials. Journal of the Korean Physical Society, 2018, 73, 805-816.	0.3	11
28	Fabry-Perot cavity resonance enabling highly polarization-sensitive double-layer gold grating. Scientific Reports, 2018, 8, 14787.	1.6	19
29	Electronic states of deep trap levels in a-plane GaN templates grown on r-plane sapphire by HVPE. Scientific Reports, 2018, 8, 7814.	1.6	5
30	Photovoltaic property of n-ZnO/p-Si heterojunctions grown by pulsed laser deposition. Thin Solid Films, 2018, 658, 22-26.	0.8	9
31	Electronic Transport Mechanism for Schottky Diodes Formed by Au/HVPE a-Plane GaN Templates Grown via In Situ GaN Nanodot Formation. Nanomaterials, 2018, 8, 397.	1.9	15
32	Locally Gated SnS ₂ /hBN Thin Film Transistors with a Broadband Photoresponse. Scientific Reports, 2018, 8, 10585.	1.6	21
33	Defect States in InP/InGaAs/InP Heterostructures by Current-Voltage Characteristics and Deep Level Transient Spectroscopy. Journal of Nanoscience and Nanotechnology, 2018, 18, 6239-6243.	0.9	2
34	Selective control of electron and hole tunneling in 2D assembly. Science Advances, 2017, 3, e1602726.	4.7	25
35	Reduction of interface traps between poly-Si and SiO ₂ layers through the dielectric recovery effect during delayed pulse bias stress. Nanotechnology, 2017, 28, 225702.	1.3	2
36	Electrical and photovoltaic properties of residue-free MoS ₂ thin films by liquid exfoliation method. Nanotechnology, 2017, 28, 195703.	1.3	18

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37	High photoresponsivity from multilayer MoS ₂ /Si heterojunction diodes formed by vertically stacking. Journal of Applied Physics, 2017, 122, .	1.1	11
38	Enhancement of near-infrared detectability from InGaZnO thin film transistor with MoS ₂ light absorbing layer. Nanotechnology, 2017, 28, 475206.	1.3	26
39	Semiconducting properties of perchlorate-doped graphene using an electrochemical method. RSC Advances, 2017, 7, 16823-16825.	1.7	4
40	Room temperature transparent conducting magnetic oxide (TCMO) properties in heavy ion doped oxide semiconductor. AIP Advances, 2017, 7, 085114.	0.6	3
41	Room temperature ferromagnetic and semiconducting properties of graphene adsorbed with cobalt oxide using electrochemical method. Journal of Magnetism and Magnetic Materials, 2017, 444, 361-363.	1.0	0
42	Electrical properties of thin film transistors with zinc tin oxide channel layer. Journal of the Korean Physical Society, 2017, 71, 500-505.	0.3	2
43	Iodide management in formamidinium-lead-halide-based perovskite layers for efficient solar cells. Science, 2017, 356, 1376-1379.	6.0	4,721
44	Structural and optical characterization of MoS ₂ quantum dots defined by thermal annealing. Journal of Luminescence, 2017, 183, 62-67.	1.5	29
45	High power conversion efficiency of intermediate band photovoltaic solar cell based on Cr-doped ZnTe. Solar Energy Materials and Solar Cells, 2017, 170, 27-32.	3.0	25
46	Room temperature ferromagnetic and ambipolar behaviors of MoS ₂ doped by manganese oxide using an electrochemical method. Applied Physics Letters, 2017, 110, .	1.5	7
47	Effect of Silver Nanoparticles with Indium Tin Oxide Thin Layers on Silicon Solar Cells. Applied Science and Convergence Technology, 2017, 26, 91-94.	0.3	2
48	Controllable Growth of Single Layer MoS ₂ and Resistance Switching Effect in Polymer/MoS ₂ Structure. Applied Science and Convergence Technology, 2017, 26, 129-132.	0.3	1
49	Effect of vanadium oxide interfacial layer for electrical contact on p-type silicon. Current Applied Physics, 2016, 16, 1315-1319.	1.1	0
50	Toward negligible charge loss in charge injection memories based on vertically integrated 2D heterostructures. Nano Research, 2016, 9, 2319-2326.	5.8	36
51	Optimization of the p+-ZnTe layer for back contacts of ZnTe thin-film solar cells. Journal of the Korean Physical Society, 2016, 69, 416-420.	0.3	5
52	Resistive switching memory device with metal-oxide quantum dots on a graphene layer. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 325-328.	0.8	0
53	Effect of space layer doping on photoelectric conversion efficiency of InAs/GaAs quantum dot solar cells. Applied Physics Letters, 2015, 107, 203503.	1.5	3
54	Electrically Tunable and Negative Schottky Barriers in Multi-layered Graphene/MoS ₂ Heterostructured Transistors. Scientific Reports, 2015, 5, 13743.	1.6	55

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55	Growth of p-type ZnTe thin films by using nitrogen doping during pulsed laser deposition. Journal of the Korean Physical Society, 2015, 67, 672-675.	0.3	10
56	Structural and optical properties of MoS ₂ layers grown by successive two-step chemical vapor deposition method. Thin Solid Films, 2015, 587, 47-51.	0.8	16
57	Properties of room-temperature ferromagnetic semiconductor in manganese-doped bilayer graphene by chemical vapor deposition. Journal of Materials Chemistry C, 2015, 3, 4235-4238.	2.7	9
58	Stable p-type properties of single walled carbon nanotubes by electrochemical doping. Physical Chemistry Chemical Physics, 2015, 17, 16243-16245.	1.3	10
59	Enhancement of photoluminescence efficiency from semi-polar InGaN/GaN multiple quantum wells with silver metal. Journal of Luminescence, 2015, 162, 115-118.	1.5	2
60	Transport properties of unrestricted carriers in bridge-channel MoS ₂ field-effect transistors. Nanoscale, 2015, 7, 17556-17562.	2.8	14
61	Magnetotransport properties of Fe/GaAlAs/GaMnAs hybrid magnetic trilayer structures. Journal of Applied Physics, 2014, 115, 17C715.	1.1	5
62	Decimal Tunneling Magnetoresistance States in Fe/GaAlAs/GaMnAs Magnetic Tunnel Junction. IEEE Transactions on Magnetics, 2014, 50, 1-4.	1.2	2
63	Reversible conductance switching characteristics in a polymer-In ₂ O ₃ nanocrystals junction. AIP Advances, 2014, 4, .	0.6	3
64	Highly Improved Sb ₂ S ₃ Sensitized Inorganic/Organic Heterojunction Solar Cells and Quantification of Traps by Deep Level Transient Spectroscopy. Advanced Functional Materials, 2014, 24, 3587-3592.	7.8	454
65	Oxygen incorporation in ZnTe thin films grown by plasma-assisted pulsed laser deposition. Current Applied Physics, 2014, 14, S49-S52.	1.1	5
66	Photoresponse of n-ZnO/p-Si photodiodes to violet-green bandwidth light caused by defect states. Thin Solid Films, 2013, 545, 517-520.	0.8	11
67	Electrical characteristics of resistive switching memory with metal oxide nanoparticles on a graphene layer. Thin Solid Films, 2013, 543, 106-109.	0.8	4
68	Electrical characterization of flash memory structure with vanadium silicide nano-particles. Journal of Alloys and Compounds, 2013, 559, 1-4.	2.8	5
69	Tunneling magnetoresistance from non-collinear alignment of magnetization in Fe/GaAlAs/GaMnAs magnetic tunnel junctions. Applied Physics Letters, 2013, 102, 212404.	1.5	14
70	Defect states of a-plane GaN grown on r-plane sapphire by controlled integration of silica nano-spheres. Journal of Crystal Growth, 2013, 370, 78-81.	0.7	7
71	Defect states in hybrid solar cells consisting of Sb ₂ S ₃ quantum dots and TiO ₂ nanoparticles. Applied Physics Letters, 2013, 103, 023901.	1.5	20
72	Quaternary memory device fabricated from a single layer Fe film. Journal of Applied Physics, 2012, 111, 07C704.	1.1	3

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73	Low operation voltage and high thermal stability of a WSi ₂ nanocrystal memory device using an Al ₂ O ₃ /HfO ₂ /Al ₂ O ₃ tunnel layer. Applied Physics Letters, 2012, 100, 072901.	1.5	16
74	Charge loss mechanism of non-volatile V ₃ Si nano-particles memory device. Applied Physics Letters, 2012, 101, 233510.	1.5	8
75	Resistive switching effect for ZnO hybrid memory with metal-oxide nanocrystals. Thin Solid Films, 2012, 521, 98-101.	0.8	4
76	Characterization of deep levels in a-plane GaN epi-layers grown using various growth techniques. Journal of Crystal Growth, 2012, 340, 23-27.	0.7	5
77	Fabrication of a n-ZnO/p-Si heterojunction diode by ultra-high vacuum magnetron sputtering. Thin Solid Films, 2012, 520, 5997-6000.	0.8	12
78	Growth of ZnTe:O Thin Films by Oxygen-Plasma-Assisted Pulsed Laser Deposition. Japanese Journal of Applied Physics, 2012, 51, 01AD04.	0.8	4
79	Speed Enhancement of WSi ₂ Nanocrystal Memory with Barrier-Engineered Si ₃ N ₄ /HfAlO Tunnel Layer. Japanese Journal of Applied Physics, 2012, 51, 06FE13.	0.8	0
80	Field enhancement effect by multi-tunnel layer in metal-silicide nanocrystals nonvolatile memory. AIP Conference Proceedings, 2011, , .	0.3	0
81	Charge loss in WSi ₂ nanocrystals nonvolatile memory with SiO ₂ /Si ₃ N ₄ /SiO ₂ tunnel layer. Current Applied Physics, 2011, 11, e6-e9.	1.1	2
82	Resistance switching properties of In ₂ O ₃ nanocrystals memory device with organic and inorganic hybrid structure. Applied Physics A: Materials Science and Processing, 2011, 102, 933-938.	1.1	8
83	Growth of high quality a-plane GaN epi-layer on r-plane sapphire substrates with optimization of multi-buffer layer. Journal of Crystal Growth, 2010, 312, 3122-3126.	0.7	15
84	Electrical properties of WSi ₂ nanocrystal memory with SiO ₂ /Si ₃ N ₄ /SiO ₂ tunnel barriers. Current Applied Physics, 2010, 10, e5-e8.	1.1	4
85	Nonpolar growth and characterization of a-plane InGaN/GaN quantum well structures with different indium compositions. Solid-State Electronics, 2010, 54, 1221-1226.	0.8	5
86	SiC nano-particles application to nano-floating gate memory. , 2010, , .		0
87	Analysis of charge loss in nonvolatile memory with multi-layered SiC nanocrystals. Applied Physics Letters, 2009, 95, 063501.	1.5	13
88	Field dependence of barrier heights and luminescence properties in polar and nonpolar InGaN/GaN single quantum wells. Applied Physics Letters, 2009, 95, 182109.	1.5	3
89	Multi-Layered SiC Nanocrystals Embedded in SiO ₂ Dielectrics for Nonvolatile Memory Application. Materials Research Society Symposia Proceedings, 2009, 1160, 1.	0.1	0
90	Fabrication and Electrical Characterization of Metal-Silicide Nanocrystals for Nano Floating Gate Nonvolatile Memory. Materials Research Society Symposia Proceedings, 2009, 1160, 1.	0.1	0

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91	Study on carrier trapping and emission processes in InAs/GaAs self-assembled quantum dots by varying filling pulse width during DLTS measurements. Superlattices and Microstructures, 2009, 46, 312-317.	1.4	9
92	Enhanced of electrical characteristics of nano-crystal floating gate memory with In ₂ O ₃ nano-particles embedded in polyimide. Journal of Electroceramics, 2009, 23, 150-153.	0.8	5
93	Nano-floating gate capacitor with SnO ₂ quantum dots distributed in polyimide dielectrics. Physica Status Solidi (B): Basic Research, 2009, 246, 893-896.	0.7	3
94	Analysis of energy levels of InAs/GaAs self-assembled quantum dots by using <i>C</i> and <i>V</i> and deep level transient spectroscopy. Physica Status Solidi (B): Basic Research, 2009, 246, 808-811.	0.7	0
95	Polarization effect on electronic band structure of InGaN/GaN multi-quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S731.	0.8	0
96	Characteristics of plasma hydrogenated ZnO films oriented along the (110) plane grown by pulsed laser deposition. Thin Solid Films, 2009, 517, 3927-3930.	0.8	4
97	Studies of defect states of ZnO thin films under different annealing conditions. Microelectronics Journal, 2009, 40, 313-315.	1.1	6
98	Study of magnetic impurity as defects in ZnO grown by pulsed laser deposition. Microelectronics Journal, 2009, 40, 283-285.	1.1	2
99	Charging effect of In ₂ O ₃ nano-particles embedded in polyimide layer for application as non-volatile nano-floating gate memory. Current Applied Physics, 2009, 9, S43-S46.	1.1	12
100	Carrier dynamics in energy states of InAs/GaAs quantum dots by measuring selective carrier filling and extracting techniques. , 2009, , .		0
101	Structural, electrical, and optical characterizations of a-plane InGaN/GaN quantum well structures. , 2009, , .		0
102	Dislocation related defect states in GaN irradiated with 1 MeV electron beam. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1630-1632.	0.8	0
103	Magnetotransport properties of GaMnAs with ferromagnetic nanodots. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1043-1046.	0.8	3
104	Characterization of electron irradiated GaN n+p diode. Thin Solid Films, 2008, 516, 3482-3485.	0.8	21
105	Relevant correlation between electrical and magnetic properties for p-type InP:Zn implanted with Mn (10 at.%). Applied Physics Letters, 2008, 93, .	1.5	1
106	Dependence of ferromagnetic properties on conductivity for As-doped p-type (Zn _{0.93} Mn _{0.07})O layers. Applied Physics Letters, 2008, 93, .	1.5	18
107	Electrical Characterization of ZnO Nano-Particles Embedded in a Polyimide for Application as a Nano-Floating Gate Memory. Journal of the Korean Physical Society, 2008, 53, 327-330.	0.3	3
108	Electrical Characterization of Nano-Floating Gate Capacitor with Silicon Carbide Nano-Particles. , 2007, , .		0

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109	Improvement of charge storage characteristics on floating gated nonvolatile memory devices with In ₂ O ₃ nanoparticles embedded polyimide gate insulator. Applied Physics Letters, 2007, 91, .	1.5	21
110	High magnetoresistance of InSb with an embedded Au core. , 2007, , .		0
111	Fabrication of Nonvolatile Nano-Floating Gate Memory with Self-Assembled Metal-Oxide Nano-Particles Embedded in Polyimide. , 2007, , .		0
112	Electrical and optical properties of p-type InMnP:Zn for nano-spintronics. , 2007, , .		0
113	Optical, structural, and magnetic properties of p-type InMnP:Zn implanted with the Mn (1 and 10Åat.%). Solid State Communications, 2007, 144, 128-133.	0.9	0
114	Optical, structural, and magnetic properties of p-type GaN implanted with Fe+(5 and 10 at%). Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 78-85.	0.8	0
115	Study on defect states using deep level transient spectroscopy of ZnO grown by pulsed laser deposition. Physica Status Solidi (B): Basic Research, 2007, 244, 1500-1503.	0.7	2
116	Enhanced Curie temperature persisting between 100 and 200K ($\sim 1/4$ 50K by theory) with Mn ($\sim 1/4$ 0.290%) based on InMnP:Zn. Journal of Crystal Growth, 2006, 297, 289-293.	0.7	3
117	Electrical properties of ZnO Nano-particles embedded in polyimide. Journal of Electronic Materials, 2006, 35, 512-515.	1.0	6
118	Electrical properties of metal-oxide semiconductor nano-particle device. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 432-435.	1.3	11
119	Magnetic properties of cobalt nanodots fabricated by a new laser irradiation method: anisotropy and superparamagnetism. IEEE Transactions on Magnetics, 2005, 41, 3313-3315.	1.2	5
120	Characterization of nanofloating gate memory with ZnO nanoparticles embedded in polymeric matrix. , 2005, , .		0
121	Electrical properties of InAs/InGaAs/GaAs quantum-dot infrared photodetectors. , 2005, , .		0
122	Photoluminescence analysis of white-emitting si nanoparticles using effective mass approximation method. , 2004, , .		0
123	Creation of deep levels in horizontal Bridgman-grown GaAs by hydrogenation. Applied Physics Letters, 1988, 53, 856-858.	1.5	41
124	Mixed Phase Confirmation of InAs _x P _{1-x} Nanowire Array Using Modified Reciprocal Space Mapping. Electronic Materials Letters, 0, , 1.	1.0	2